

FORM PTO-1595

(Rev. 08/05)

Office OMB No. 0651-0027 (exp. 06/30/2008)

RECORDATION FORM COVER SHEET

U.S. DEPARTMENT OF COMMERCE
United States Patent and Trademark

PATENTS ONLY

To the Director of the U.S. Patent and Trademark Office: Please record the attached documents or the new address(es) below.

1. Name of conveying party(ies):

Avogy, Inc.
677 River Oaks Parkway
San Jose, CA 95134Additional name(s) of conveying party(ies) attached? ☐ Yes ☒ No

3. Nature of conveyance/Execution Date(s):

Execution Date: 03/21/14

- ☐ Assignment ☐ Merger
☒ Security Agreement ☐ Change of Name
☐ Joint Research Agreement
☐ Government Interest Assignment
☐ Executive Order 9424, Confirmatory License
☐ Other _____

2. Name and address of receiving party(ies):

Name: Silicon Valley Bank

Internal Address:

Street Address: 3003 Tasman Dr HF 150

City: Santa Clara

State: CA

Country: USA Zip: 95054

Additional name(s) & address(es) attached? ☐ Yes ☒ No

4. Application or patent number(s):

☐ This document is being filed together with a new application.

A. Patent Application No.(s)

13079710	PCTUS2012049549	13198666	13267552
13180738	13198659	13225345	13270606
13301165	PCTUS1249520	PCTUS2012062728	PCTUS2012056101
13326192	PCTUS2012048194	13289219	13240877
13198655	13198661	13935345	13270625

B. Patent No.(s)

Additional numbers attached? ☒ Yes ☐ No

5. Name and address of party to whom correspondence concerning document should be mailed:

Name: UCC Direct Services

Internal Address: Attn: 14080632

Street Address: 187 Wolf Road, Suite 101

City: Albany

State: NY

Zip: 12205

Phone Number: 1-800-342-3676 X 4065

Fax Number: 800-962-7049

Email Address: cls-udsalbany@wolterskluwer.com

6. Total number of applications and patents involved: 79

7. Total fee (37 CFR 1.21 (h) & 3.41) \$3,160-

- ☒ Authorized to be charged by credit card
☐ Authorized to be charged to deposit account
☐ Enclosed
☐ None required (government interest not affecting title)

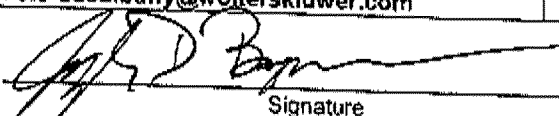
8. Payment Information

a. Credit Card Last 4 Numbers 0974
Expiration Date 3/17

b. Deposit Account Number

Authorized User Name

9. Signature:



Signature

Joseph D. Borgman

Name of Person Signing

3-31-14

Date

Total number of pages including cover sheet, attachments, and documents:

Documents to be recorded (including cover sheet) should be faxed to (571) 273-0140, or mailed to:
Mail Stop Assignment Recordation Services, Director of the USPTO, P.O. Box 1450, Alexandria, V.A. 22313-1450

OP \$3160.00 13079710

PCTUS201259245	13468325	14071032
13315705	13468332	14095759
13300009	13675694	14083217
13300028	13552365	
14062724	PCTUS2013053702	
13312055	13572408	
13299227	13586330	
13932290	PCTUS2013053751	
PCTUS2012065954	13585121	
13335572	13611467	
PCTUS2012068972	13692717	
13335329	13571743	
13307108	13675916	
14061741	13689574	
PCTUS201259250	PCTUS2013069469	
13270641	13675826	
PCTUS2012062717	PCTUS2013071522	
13299254	13731872	
13335355	PCTUS2013076007	
13315720	13735897	
PCTUS2012066669	13730619	
PCTUS2012069251	PCTUS2013076009	
13334742	13735912	
13465812	13721542	
PCTUS2012069299	14077039	
13334514	13866286	
13335383	13901546	
13529822	14045708	

INTELLECTUAL PROPERTY SECURITY AGREEMENT

This Intellectual Property Security Agreement ("Agreement") is entered into as of the Effective Date by and between SILICON VALLEY BANK ("Bank") and AVOGY, INC. ("Grantor").

RECITALS

A. Bank has agreed to make certain advances of money and to extend certain financial accommodation to Grantor (the "Loans") in the amounts and manner set forth in that certain Loan and Security Agreement by and between Bank and Grantor dated the Effective Date (as the same may be amended, modified or supplemented from time to time, the "Loan Agreement"; capitalized terms used herein are used as defined in the Loan Agreement). Bank is willing to make the Loans to Grantor, but only upon the condition, among others, that Grantor shall grant to Bank a security interest in certain Copyrights, Trademarks, Patents, and Mask Works (as each term is described below) to secure the obligations of Grantor under the Loan Agreement.

B. Pursuant to the terms of the Loan Agreement, Grantor has granted to Bank a security interest in all of Grantor's right, title and interest, whether presently existing or hereafter acquired, in, to and under all of the Collateral.

NOW, THEREFORE, for good and valuable consideration, receipt of which is hereby acknowledged, and intending to be legally bound, as collateral security for the prompt and complete payment when due of its obligations under the Loan Agreement, Grantor hereby represents, warrants, covenants and agrees as follows:

AGREEMENT

1. Grant of Security Interest. To secure its obligations under the Loan Agreement, Grantor grants and pledges to Bank a security interest in all of Grantor's right, title and interest in, to and under its intellectual property (all of which shall collectively be called the "Intellectual Property Collateral"), including, without limitation, the following:

(a) Any and all copyright rights, copyright applications, copyright registrations and like protections in each work or authorship and derivative work thereof, whether published or unpublished and whether or not the same also constitutes a trade secret, now or hereafter existing, created, acquired or held, including without limitation those set forth on Exhibit A attached hereto (collectively, the "Copyrights");

(b) Any and all trade secrets, and any and all intellectual property rights in computer software and computer software products now or hereafter existing, created, acquired or held;

(c) Any and all design rights that may be available to Grantor now or hereafter existing, created, acquired or held;

(d) All patents, patent applications and like protections including, without limitation, improvements, divisions, continuations, renewals, reissues, extensions and continuations-in-part of the same, including without limitation the patents and patent applications set forth on Exhibit B attached hereto (collectively, the "Patents");

(e) Any trademark and servicemark rights, whether registered or not, applications to register and registrations of the same and like protections, and the entire goodwill of the business of Grantor

connected with and symbolized by such trademarks, including without limitation those set forth on Exhibit C attached hereto (collectively, the "Trademarks");

(f) All mask works or similar rights available for the protection of semiconductor chips, now owned or hereafter acquired, including, without limitation those set forth on Exhibit D attached hereto (collectively, the "Mask Works");

(g) Any and all claims for damages by way of past, present and future infringements of any of the rights included above, with the right, but not the obligation, to sue for and collect such damages for said use or infringement of the intellectual property rights identified above;

(h) All licenses or other rights to use any of the Copyrights, Patents, Trademarks, or Mask Works and all license fees and royalties arising from such use to the extent permitted by such license or rights;

(i) All amendments, extensions, renewals and extensions of any of the Copyrights, Trademarks, Patents, or Mask Works; and

(j) All proceeds and products of the foregoing, including without limitation all payments under insurance or any indemnity or warranty payable in respect of any of the foregoing;

provided that, notwithstanding anything contained in this Agreement to the contrary, the term "Intellectual Property Collateral" shall not include: (i) any rights held under a license that are not assignable by their terms without the consent of the licensor thereof (but only to the extent such restriction on assignment is enforceable under applicable law), provided, however, that upon termination of such prohibition, such interest shall immediately become Intellectual Property Collateral without any action of Grantor or Bank and the exclusions of this clause (i) shall in no way be construed to limit, impair, or otherwise affect Bank's continuing security interests in and liens upon any rights or interests of Grantor in or to all accounts, license and royalty fees and other revenues, proceeds, or income arising out of or relating to any license or the foregoing intellectual property; and (ii) any United States intent-to-use trademark applications to the extent that, and solely during the period in which, the grant of a security interest therein would impair the validity or enforceability of such intent-to-use trademark applications under applicable federal law, provided that upon submission and acceptance by the United States Patent and Trademark Office of an amendment to allege use pursuant to 15 U.S.C. Section 1060(a) (or any successor provision), such intent-to-use trademark application shall be considered Intellectual Property Collateral.

2. Recordation. Grantor authorizes the Commissioner for Patents, the Commissioner for Trademarks and the Register of Copyrights and any other government officials to record and register this Agreement upon request by Bank.

3. Authorization. Grantor hereby authorizes Bank to (a) modify this Agreement unilaterally by amending the exhibits to this Agreement to include any Intellectual Property Collateral which Grantor obtains subsequent to the date of this Agreement, and (b) file a duplicate original of this Agreement containing amended exhibits reflecting such new Intellectual Property Collateral.

4. Loan Documents. This Agreement has been entered into pursuant to and in conjunction with the Loan Agreement, which is hereby incorporated by reference. The provisions of the Loan Agreement shall supersede and control over any conflicting or inconsistent provision herein. The rights and remedies of Bank with respect to the Intellectual Property Collateral are as provided by the Loan Agreement and related documents, and nothing in this Agreement shall be deemed to limit such rights and remedies.

5. Execution in Counterparts. This Agreement may be executed in counterparts (and by different parties hereto in different counterparts), each of which shall constitute an original, but all of which when taken together shall constitute a single contract. Delivery of an executed counterpart of a signature page to this Agreement by facsimile or in electronic (i.e., "pdf" or "tif" format) shall be effective as delivery of a manually executed counterpart of this Agreement.

6. Successors and Assigns. This Agreement will be binding on and shall inure to the benefit of the parties hereto and their respective successors and assigns.

7. Governing Law. This Agreement and any claim, controversy, dispute or cause of action (whether in contract or tort or otherwise) based upon, arising out of or relating to this Agreement and the transactions contemplated hereby and thereby shall be governed by, and construed in accordance with, the laws of the United States and the State of California, without giving effect to any choice or conflict of law provision or rule (whether of the State of California or any other jurisdiction).

IN WITNESS WHEREOF, the parties have caused this Intellectual Property Security Agreement to be duly executed by its officers thereunto duly authorized as of the first date written above.

GRANTOR:

AVOCY, INC.

By: DINESH KRISHNATHAN
Title: CEO

BANK:

SILICON VALLEY BANK

By: _____
Title: _____

IN WITNESS WHEREOF, the parties have caused this Intellectual Property Security Agreement to be duly executed by its officers hereunto duly authorized as of the first date written above.

GRANTOR:

AVOGY, INC.

By: _____
Title: _____

BANK:

SILICON VALLEY BANK

Uli M. Maitra
By: MONA MITRA
Title: VICE PRESIDENT

EXHIBIT A

Copyrights

N/A

EXHIBIT B

Patents

FILE NO.	IF FAMILY NO.	CLIENT REF. NO.	TITLE	COUNTRY	APPL. NO.	FILING DATE	PUB NO.	PUB DATE	PATENT NO.	ISSUE DATE	STATUS	INVENTORS
93444-818757	00010008	EP80001	CONTROLLED DOPING IN ILI-MATERIALS	United States of America	13079710	4/4/11	0248577-A1	10/4/12			Published	Linda T. Romano, Dave P. Bour, Isik C. Kizilyalli, Hui Nie, Thomas R. Prunty
93444-818760	00030008	EP80001	ELECTRICAL ISOLATION OF HIGH DENSITY REGIONS IN A SEMICONDUCTOR DEVICE	United States of America	13180758	7/12/11	US-2013-0612502-A1	1/17/13			Published	Isik C. Kizilyalli, Dave P. Bour, Richard J. Brown, Andrew P. Edwards, Hui Nie, Linda Romano
93444-826397	00040008	EP80004	EDGE TERMINATION BY ION IMPLANTATION IN GAN	United States of America	13301165	11/21/11	US-2013-0126886-A1				Published	Isik C. Kizilyalli, Hui Nie, Andrew P. Edwards, Linda Romano, Dave P. Bour, Richard J. Brown, Thomas R. Prunty
93444-826389	00050008	EP80005	INGAN ORBIC SOURCE CONTACTS FOR VERTICAL POWER DEVICES	United States of America	13326192	12/14/11	US-2013-0153917-A1				Published	Linda Romano, Andrew P. Edwards, Dave P. Bour, Isik C. Kizilyalli
93444-808244	00060008	EP80006	METHOD AND SYSTEM FOR A GAN VERTICAL JET UTILIZING A REGROWN GATE	United States of America	13198653	8/4/11	US-2013-0052811-A1	2/7/13			Published	Isik C. Kizilyalli, Hui Nie, Andrew P. Edwards, Linda Romano, Dave P. Bour, Richard J. Brown, Thomas R. Prunty
93444-816395	000610PC	EP80006PC	METHOD AND SYSTEM FOR A GAN VERTICAL JET UTILIZING A REGROWN GATE	PCT	PCT/US2012049549	8/3/12	WO 2013/020061	2/7/13			Published	Isik C. Kizilyalli, Hui Nie, Andrew P. Edwards, Linda Romano, Dave P. Bour, Richard J. Brown, Thomas R. Prunty

93444- 808236	0007000US	EP8- 0007	METHOD AND SYSTEM FOR A GAN VERTICAL JET UTILIZING A REGROWN CHANNEL	United States of America	13198659	8/4/11	US-2013- 0032812-A1	2/7/13	Published	Isik C. Kizilyall, Hui Nie, Andrew P. Edwards, Linda Romano, Dave P. Bour, Richard J. Brown, Thomas R. Prunty
93444- 846589	000710PC	EP8- 0007PC	METHOD AND SYSTEM FOR A GAN VERTICAL JET UTILIZING A REGROWN CHANNEL	PCT	PCT/US1249520	8/3/12	WO 2013/020051	2/7/13	Published	Isik C. Kizilyall, Hui Nie, Andrew P. Edwards, Linda Romano, Dave P. Bour, Richard J. Brown, Thomas R. Prunty
93444- 846593	000800PC	EP8- 0008PC	METHOD AND SYSTEM FOR DOPING CONTROL IN GALLIUM NITRIDE BASED DEVICES	PCT	PCT/US2012048104	7/25/12	WO 2013/019521	2/7/13	Published	Isik C. Kizilyall, Hui Nie, Andrew P. Edwards, Linda Romano, Dave P. Bour, Richard J. Brown, Thomas R. Prunty
93444- 808237	000800US	EP8- 0008	METHOD AND SYSTEM FOR DOPING CONTROL IN GALLIUM NITRIDE BASED DEVICES	United States of America	13198661	8/4/11	US-2013- 0032813-A1	2/7/13	Published	Isik C. Kizilyall, Hui Nie, Andrew P. Edwards, Linda Romano, Dave P. Bour, Richard J. Brown, Thomas R. Prunty
93444- 808232	000900US	EP80009	METHOD AND SYSTEM FOR FORMATION OF P- N JUNCTIONS IN GALLIUM NITRIDE BASED ELECTRONICS	United States of America	13198666	8/4/11	US-2013- 0032814-A1	2/7/13	Published	David P. Bour, Thomas R. Prunty, Linda Romano, Andrew P. Edwards, Isik C. Kizilyall, Hui Nie, Richard J. Brown, Madhan M. Raj
93444- 808243	001000US	EP80010	METHOD AND SYSTEM FOR LOCAL CONTROL OF DEFECT DENSITY IN GALLIUM NITRIDE BASED ELECTRONICS	United States of America	13225345	9/27/11	US-2013- 0056743-A1		Published	David P. Bour, Linda Romano, Thomas R. Prunty, Isik C. Kizilyall, Hui Nie, Andrew P. Edwards, Richard J. Brown

93444- 856390	001100PC	EP5- 011PC	MONOLITHICALLY INTEGRATED VERTICAL JET AND SCHOTTKY DIODE	PCT	PCTUS2012062728	10/31/12	WO 2013/066967	Published	Isik C, Kizilyalli, Hui Nie, Andrew P, Edwards, Linda Romano, Dave P, Bour, Richard J, Brown, Thomas R, Prunty
93444- 813831	001100US	EP5001	MONOLITHICALLY INTEGRATED VERTICAL JET AND SCHOTTKY DIODE	United States of America	13289219	11/4/11	US-2013- 0112983-A1	Issued	Isik C, Kizilyalli, Hui Nie, Andrew P, Edwards, Linda Romano, David P, Bour, Richard J, Brown, Thomas R, Prunty
93444- 880165	001100US	EP5- 0011-1	MONOLITHICALLY INTEGRATED VERTICAL JET AND SCHOTTKY DIODE	United States of America	13915345	7/3/13		Pending	Isik C, Kizilyalli, Hui Nie, Andrew P, Edwards, Linda Romano, Dave P, Bour, Richard J, Brown, Thomas R, Prunty
93444- 813833	001200US	EP50012	MONOLITHICALLY INTEGRATED HEAT AND SCHOTTKY DIODE	United States of America	13267352	10/6/11	US-2013- 0067803-A1	Published	Kizilyalli Isik C, Nie Hui, Edwards Andrew P., Romano Linda, David P Bour, Brown Richard J., Prunty Thomas R.
93444- 816904	001300US	EP50013	METHOD AND SYSTEM FOR FLOATING GUARD RINGS IN GAN MATERIALS	United States of America	13270606	10/11/11	US-2013- 0087835-A1	Published	Andrew P, Edwards, Hui Nie, Isik C, Kizilyalli, Richard J, Brown, Dave P, Bour, Linda Romano, Thomas R, Prunty
93444- 852922	001400PC		METHOD AND SYSTEM FOR DIFFUSION AND IMPLANTATION IN GALLIUM NITRIDE BASED DEVICES	PCT	PCTUS2012056101	9/19/12		Pending	Dave P, Bour, Richard J, Brown, Isik C, Kizilyalli, Thomas R, Prunty, Linda Romano, Andrew P, Edwards, Hui Nie, Medhen M, Raj

93444- 816905	001400US	EP890014	METHOD AND SYSTEM FOR DIFFUSION AND IMPLANTATION IN GALLIUM NITRIDE BASED DEVICES	United States of America	13240877	9/22/11	US-2013- 0075746-A1	3/28/13	Published	Dave P. Bour, Richard J. Brown, Jink C. Kizilyelli, Thomas R. Prunty, Linda Romano, Andrew P. Edwards, Hui Nie, Matthew M. Raj
93444- 819244	001500US	EP8- 0015	METHOD OF FABRICATING A GALLIUM NITRIDE MERGED P-LIN SCHOTTKY (MPS) DIODE	United States of America	13270625	10/11/11	US-2013- 0087878-A1	4/11/13	Published	Andrew P. Edwards, Hui Nie, Jink C. Kizilyelli, Linda Romano, Dave P. Bour, Richard J. Brown, Thomas R. Prunty
93444- 851214	001510PC	EP8- 0015PC	METHOD OF FABRICATING A GAN MERGED P-LIN SCHOTTKY (MPS) DIODE	PCT	PCT/US201259245	10/8/12	WO 2013/0255629		Published	Andrew P. Edwards, Hui Nie, Jink C. Kizilyelli, Linda Romano, Dave P. Bour, Richard J. Brown, Thomas R. Prunty
93444- 819311	001600US	EP890016	VERTICAL GAN-BASED METAL INSULATOR SEMICONDUCTOR FET	United States of America	13315705	12/9/11	US-2013- 0146885-A1	8/5/8242	Issued	Richard J. Brown, Hui Nie, Andrew Edwards, Jink Kizilyelli, David Bour, Thomas Prunty, Linda Romano, Matthew Raj
93444- 819313	001700US	EP890017	GAN-BASED SCHOTTKY BARRIER DIODE WITH ALGAN SURFACE LAYER	United States of America	13300009	11/18/11	US-2013- 0120880-A1		Published	Richard J. Brown, Thomas R. Prunty, Dave P. Bour, Jink C. Kizilyelli, Hui Nie, Andrew P. Edwards, Linda Romano, Matthew M. Raj
93444- 819312	001800US	EP890018	GAN-BASED SCHOTTKY BARRIER DIODE WITH FIELD PLATE	United States of America	13300028	11/18/11	US-2013- 0122006-A1	8643134	Issued	Matthew Raj, Richard J. Brown, Thomas R. Prunty, David P. Bour, Jink C. Kizilyelli, Hui Nie, Andrew P. Edwards, Linda Romano

93444- 8391731	001801US	GAN-BASED SCHOTTKY BARRIER DIODE WITH FIELD PLATE	United States of America	14062724	10/24/13	US-2014- 0051236-A1	Published	Madhan Raj, Richard J. Brown, Thomas R. Prueny, David P., Bour, Isk C., Kizilyalli, Hui Nie, Andrew P. Edwards, Ikeda Romano
93444- 819314	001900US	IN-SITU SiN GROWTH TO ENABLE SCHOTTKY CONTACT FOR GAN DEVICES	United States of America	13312055	12/6/11	US-2013- 0143392-A1	Published	Linda Romano, Dave P. Bour, Andrew P. Edwards, Hui Nie, Isk C., Kizilyalli, Richard J. Brown, Thomas R. Prueny
93444- 819315	002090US	ALUMINUM GALLIUM NITRIDE ETC STOP LAYER FOR GALLIUM NITRIDE BASES DEVICES	United States of America	13292227	11/17/11	US-2013- 0126884-A1	Published	Linda Romano, Andrew P., Edwards, Richard J. Brown, Dave P., Bour, Hui Nie, Isk C. Kizilyalli, Thomas R. Prueny, Madhan M. Raj
93444- 832983	002010US	ALUMINUM GALLIUM NITRIDE ETC STOP LAYER FOR GALLIUM NITRIDE BASED DEVICES	United States of America	13932290	7/1/13		Pending	Linda Romano, Andrew P., Edwards, Richard J. Brown, David P., Bour, Hui Nie, Isk C. Kizilyalli, Thomas R. Prueny, Madhan Raj
93444- 832984	002100PC	METHOD AND SYSTEM FOR A GAN SELF- ALIGNED VERTICAL MESFET	PCT	PCTUS2012065954	11/20/12	WO 2013095847	Published	Richard J. Brown, Isk C., Kizilyalli, Hui Nie, Andrew P., Edwards, Dave P., Bour
93444- 832990	002100US	METHOD AND SYSTEM FOR A GAN SELF- ALIGNED VERTICAL MESFET	United States of America	13335572	12/22/11	US-2013- 0161635-A1	Published	Richard J. Brown, Isk C., Kizilyalli, Hui Nie, Andrew P., Edwards, Dave P., Bour
93444- 839134	002200PC	METHOD OF FABRICATING A GALLIUM NITRIDE P-L-N DIODE USING IMPLANTATION	PCT	PCTUS2012068972	12/11/12	WO 2013096013	Published	Isk C., Kizilyalli, Hui Nie, Andrew P. Edwards, Richard J. Brown, Donald R. Dassary
93444- 819316	002200US	METHOD OF FABRICATING A GAN P- N DIODE USING IMPLANTATION	United States of America	13335929	12/22/11	US-2013- 0161780-A1	Published	Isk C., Kizilyalli, Hui Nie, Andrew P. Edwards, Richard J. Brown, Donald R. Dassary

93444- 824391	002300US	EP80023	METHOD AND SYSTEM FOR CARBON DOPING CONTROL IN GALLIUM NITRIDE BASED DEVICES	United States of America	13307106	11/30/11	US-2013- 0137225-A1	8369153	10/29/13	Issued	David P. Bour, Thomas R. Prunty, Linda Romano, Richard J. Brown, Isik C. Kizilyelli, Hui Nig
93444- 821183	002310US	EP8- 0023-1	METHOD AND SYSTEM FOR CARBON DOPING CONTROL IN GALLIUM NITRIDE BASED DEVICES	United States of America	14061741	10/23/13				Pending	David P. Bour, Thomas R. Prunty, Linda Romano, Richard J. Brown, Isik C. Kizilyelli, Hui Nig
93444- 834261	002400PC	EP8- 0024PC	SCHOTTKY DIODE WITH BURIED LAYER IN GAN MATERIALS	PCT	PCTUS201239250	10/8/12	WO 2013055631			Published	Andrew P. Edwards, Hui Nig, Isik C. Kizilyelli, Richard J. Brown, David P. Bour, Linda Romano, Thomas R. Prunty
93444- 822319	002400US	EP-0024	SCHOTTKY DIODE WITH BURIED LAYER IN GAN MATERIALS	United States of America	13270641	10/11/11	US-2013- 0987879-A1		4/11/13	Published	Andrew P. Edwards, Hui Nig, Isik C. Kizilyelli, Richard J. Brown, Dave P. Bour, Linda Romano, Thomas R. Prunty
93444- 836389	002500PC	EP8- 0025PC	METHOD AND SYSTEM FABRICATING FLOATING GUARD RINGS IN GAN MATERIALS	PCT	PCTUS2012062717	10/31/12	WO 2013074291			Published	Donald R. Disney, Andrew P. Edwards, Hui Nig, Richard J. Brown, Isik C. Kizilyelli, Dave P. Bour, Linda Romano, Thomas R. Prunty
93444- 823930	002500US	EP8- 0025	METHOD AND SYSTEM FOR FABRICATING FLOATING GUARD RINGS IN GAN MATERIALS	United States of America	13292254	11/17/11	US-2013- 0126865-A1			Allowed	Donald R. Disney, Andrew P. Edwards, Hui Nig, Richard J. Brown, Isik C. Kizilyelli, Dave P. Bour, Linda Romano, Thomas R. Prunty
93444- 824394	002600US	EP80026	FABRICATION OF FLOATING GUARD RINGS USING SELECTIVE REGROWTH	United States of America	13333353	12/22/11	US-2013- 0164893-A1	8592298	11/26/13	Issued	Linda Romano, David P. Bour, Andrew Edwards, Hui Nig, Isik C. Kizilyelli, Richard J. Brown, Thomas R. Prunty

93444- 824395	002700US	IPS- 0027	VERTICAL GAN FET WITH GATE SOURCE ELECTRODES ON REGROWN GATE	United States of America	13315720	12/9/11	US-2013- 0146886-A1	Allowed	Donald R. Disney, Hui Nie, Isik C. Kizlyall, Richard J. Brown
93444- 837888	002710PC	IPS- 0027PC	VERTICAL GAN FET WITH GATE AND SOURCE ELECTRODES ON REGROWN GATE	PCT	PCTUS2012066669	11/27/12	WO 2013/085748	Published	Donald R. Disney, Hui Nie, Isik C. Kizlyall, Richard J. Brown
93444- 837874	002600PC	IPS- 0026PC	METHOD AND SYSTEM FOR JUNCTION TERMINATION IN GAN MATERIALS USING CONDUCTIVITY MODULATION	PCT	PCTUS2012069251	12/12/12	WO 2013/096054	Published	Hui Nie, Andrew P. Edwards, Donald R. Disney, Richard J. Brown, Isik C. Kizlyall
93444- 826382	002600US	IPS- 0026	METHOD AND SYSTEM FOR JUNCTION TERMINATION IN GAN MATERIALS USING CONDUCTIVITY MODULATION	United States of America	13334742	12/22/11	US-2013- 0161633-A1	Allowed	Hui Nie, Andrew P. Edwards, Donald R. Disney, Richard J. Brown, Isik C. Kizlyall
93444- 826381	002900US	IPS- 0029	METHOD AND SYSTEM FOR PLANAR REGROWTH IN GAN ELECTRONIC DEVICES	United States of America	13465812	5/7/12	US-2013- 0292686-A1	Published	Isik C. Kizlyall, Linda Romano, Dave P. Bour
93444- 859133	003090PC	IPS- 0030PC	METHOD AND SYSTEM FOR A GALLIUM NITRIDE VERTICAL FET WITH SELF- ALIGNED SOURCE AND GATE	PCT	PCTUS2012069299	12/12/12	WO 2013/096062	Published	Donald R. Disney, Isik C. Kizlyall, Hui Nie, Linda Romano, Richard J. Brown, Madhan M. Raj
93444- 836389	003000US	IPS- 0030	METHOD AND SYSTEM FOR A GAN VERTICAL FET WITH SELF- ALIGNED SOURCE AND GATE	United States of America	13334514	12/22/11	US-2013- 0161705-A1	Published	Donald R. Disney, Isik C. Kizlyall, Hui Nie, Linda Romano, Richard J. Brown, Madhan M. Raj
93444- 836379	003100US	IPS- 0031	METHOD AND SYSTEM FOR FABRICATING EDGE TERMINATION STRUCTURES IN GAN MATERIALS	United States of America	13335383	12/22/11	US-2013- 0161634-A1	Allowed	Donald R. Disney, Isik C. Kizlyall, Linda Romano, Andrew P. Edwards, Hui Nie
93444- 833448	003200US	IPS- 0032	GAN VERTICAL SUPERJUNCTION DEVICE STRUCTURE AND FABRICATION METHODS	United States of America	13529822	6/21/12	US-2013- 0341677-A1	Published	Hui Nie, Andrew P. Edwards, Donald R. Disney, Isik C. Kizlyall

93444- 833469	003300US	EP8- 0033	METHOD AND SYSTEM FOR A GALLIUM NITRIDE VERTICAL JET WITH SELF- ALIGNED GATE METALLIZATION	United States of America	13468325	5/10/12	US-2013- 0299873-A1	Allowed	Donald R. Disney, Richard J. Brown, Hui Nie
93444- 839418	003310US	EP8- 0033.1	METHOD AND SYSTEM FOR A GAN VERTICAL JET WITH SELF- ALIGNED SOURCE METALLIZATION	United States of America	13468332	5/10/12	US-2013- 0299882-A1	Allowed	Donald R. Disney, Richard J. Brown, Hui Nie
93444- 833463	003400US	EP9- 0034	VERTICAL GAN JET WITH LOW GATE DRAIN CAPACTANCE AND HIGH GATE SOURCE CAPACTANCE	United States of America	13675694	11/13/12		Pending	Donald R. Disney
93444- 820540	003900US	EP8- 0035	GAN POWER DEVICE WITH SOLIDIFIABLE BACK METAL	United States of America	13552365	7/18/12	US-2014- 0921479-A1	Published	Patrick James Lardo Hyland, Brian Alvarez, Donald R. Disney
93444- 863361	003600PC	EP8- 0036-PC	METHOD AND SYSTEM FOR GALLIUM NITRIDE ELECTRONIC DEVICES USING ENGINEERED SUBSTRATES	PCT	PCTUS2013051792	8/6/13	W/O 2014025172	Published	Hui Nie, Donald R. Disney, Isik C. Kizilyalli
93444- 840541	003600US	EP8- 0036	METHOD AND SYSTEM FOR GALLIUM NITRIDE ELECTRONIC DEVICES USING ENGINEERED SUBSTRATES	United States of America	13572408	8/10/12	US-2014- 0042447-A1	Published	Hui Nie, Donald R. Disney, Isik C. Kizilyalli
93444- 840542	003700US	EP8- 0037	METHOD AND SYSTEM FOR EDGE TERMINATION IN GAN MATERIALS BY SELECTIVE AREA IMPLANTATION DOPING	United States of America	13586330	8/15/12	US-2014- 0948903-A1	Published	Andrew Edwards, Hui Nie, Isik C. Kizilyalli, Dave Bour
93444- 883362	003800PC	EP8- 0038-PC	METHOD OF FABRICATING A GALLIUM NITRIDE MERGED P-IN SCHOTTKY (MPS) DIODE BY REGROWTH AND ETCH BACK	PCT	PCTUS2013053751	8/6/13		Pending	Madhan M. Raj, Brian Alvarez, Dave P. Bour, Andrew P. Edwards, Hui Nie, Isik C. Kizilyalli

93444- 840343	003800US	EP- 0038	METHOD OF FABRICATING A GALLIUM NITRIDE MERGED P-I-N SCHOTTKY (MPS) DIODE BY REGROWTH AND ETCH BACK BONDABLE TOP METAL CONTACTS FOR GALLIUM NITRIDE POWER DEVICES	United States of America	13585121	8/14/12	US-2014- 0048902-A1	Published	Madhan M. Raj, Brian Alvaraz, Dave P. Bour, Andrew P. Edwards, Hui Nie, Jink C. Kizilyalli
93444- 843972	003900US	EP- 0039	AC-DC CONVERTER FOR WIDE RANGE OUTPUT VOLTAGE AND HIGH SWITCHING FREQUENCY METHOD AND SYSTEM FOR IN-SITU AND REGROWTH IN GALLIUM NITRIDE BASED DEVICES	United States of America	1361467	9/12/12		Pending	Brian Joel Alvaraz, Doreald R. Dismey, Hui Nie, Patrick James Lazlo Hysaui
93444- 843971	004000US	EP- 0040	AC-DC CONVERTER FOR WIDE RANGE OUTPUT VOLTAGE AND HIGH SWITCHING FREQUENCY METHOD AND SYSTEM FOR IN-SITU AND REGROWTH IN GALLIUM NITRIDE BASED DEVICES	United States of America	13692717	12/3/12		Pending	Sittithong Angkitarakul, Hemal N. Shah
93444- 843980	004100US	EP- 0041	AC-DC CONVERTER FOR WIDE RANGE OUTPUT VOLTAGE AND HIGH SWITCHING FREQUENCY METHOD AND SYSTEM FOR IN-SITU AND REGROWTH IN GALLIUM NITRIDE BASED DEVICES	United States of America	13571743	8/1/07	US-2014- 0040306-A1	Published	David P. Bour, Thomas R. Prunty, Hui Nie, Madhan M. Raj
93444- 851061	004200US	EP- 0042	GAN VERTICAL BIPOLAR TRANSISTOR	United States of America	13675916	11/13/12		Pending	Hui Nie, Andrew P. Edwards, Jink C. Kizilyalli, Dave Bour
93444- 851060	004300US	EP- 0043	METHOD AND SYSTEM FOR GALLIUM NITRIDE VERTICAL JFET WITH SEPARATED GATE AND SOURCE	United States of America	13689574	11/20/12		Pending	Hui Nie, Andrew P. Edwards, Dave P. Bour, Jink C. Kizilyalli, Richard J. Brown, Thomas R. Prunty
93444- 892931	004400PC	EP- 0044	LATERAL GAN JFET WITH VERTICAL DRIIFT REGION	PCT	PCTUS2013069469	11/11/13		Pending	Hui Nie, Andrew Edwards, Jink Kizilyalli, Dave Bour, Thomas R. Prunty
93444- 851059	004400US	EP- 0044	LATERAL GAN JFET WITH VERTICAL DRIIFT REGION	United States of America	13675826	11/13/12		Pending	Hui Nie, Andrew P. Edwards, Jink Kizilyalli, Dave Bour, Thomas R. Prunty
93444- 894129	004500PC	EP- 0045-PC	HIGH POWER DENSITY OFF-LINE POWER SUPPLY	PCT	PCTUS2013071522	11/22/13		Pending	Hemal N. Shah
93444- 851058	004500US	EP- 0045	HIGH POWER DENSITY OFF-LINE POWER SUPPLY	United States of America	13731872	12/31/12		Pending	Hemal N. Shah

93444- 835615	004600PC	EP- 0046-PC	GALLIUM NITRIDE VERTICAL JET WITH HEXAGONAL CELL STRUCTURE	PCT	PCTUS2013076007	12/18/13	Pending	Andrew P. Edwards, Hui Nie, Donald R. Disney, Isik C. Kizilyalli
93444- 8356292	004600US	EP- 0046	GALLIUM NITRIDE VERTICAL JET WITH HEXAGONAL CELL STRUCTURE	United States of America	13735897	1/7/13	Pending	Andrew P. Edwards, Hui Nie, Donald R. Disney, Isik C. Kizilyalli
93444- 8356301	004700US	EP- 0047	METHOD AND SYSTEM FOR CO-PACKAGING GALLIUM NITRIDE ELECTRONICS	United States of America	13730619	12/28/12	Pending	Donald R. Disney, Hemanth N. Shah
93444- 835614	004800PC	EP- 0048-PC	METHOD AND SYSTEM FOR A GALLIUM NITRIDE VERTICAL TRANSISTOR	PCT	PCTUS2013076009	12/18/13	Pending	Hui Nie, Andrew P. Edwards, Isik C. Kizilyalli, Dave P. Bour, Thomas R. Pronny, Quentin Diack
93444- 8356300	004800US	EP- 0048	METHOD AND SYSTEM FOR A GALLIUM NITRIDE VERTICAL TRANSISTOR	United States of America	13735912	1/7/13	Pending	Hui Nie, Andrew P. Edwards, Isik C. Kizilyalli, Dave P. Bour, Thomas R. Pronny, Quentin Diack
93444- 8356302	004900US	EP- 0049	VERTICAL GAN POWER DEVICE WITH BREAKDOWN VOLTAGE CONTROL	United States of America	13721542	12/20/12	Pending	Donald R. Disney
93444- 8356145	005000US	EP- 0050	GALLIUM NITRIDE FIELD EFFECT TRANSISTOR WITH BURIED FIELD PLATE PROTECTED LATERAL CHANNEL	United States of America	14077039	11/7/13	Pending	Ozgur Akten, Isik C. Kizilyalli
93444- 8356147	005200US	EP- 0052	METHOD OF FABRICATING A MERGED P-N JUNCTION AND SCHOTTKY DIODE WITH REDUCED GALLIUM NITRIDE LAYER	United States of America	13865286	4/19/13	Pending	Isik C. Kizilyalli, Dave P. Bour, Thomas R. Pronny, Hui Nie, Quentin Diack, Ozgur Akten
93444- 8356300	005300US	EP- 0053	METHOD AND SYSTEM FOR CO-PACKAGING VERTICAL GALLIUM NITRIDE POWER DEVICES	United States of America	13901546	5/23/13	Pending	Donald R. Disney, Hemanth N. Shah

23444- 873691	0054000US	EP5- 0054	METHOD AND SYSTEM FOR OPERATING GALLIUMNITRIDE ELECTRONICS	United States of America	14035708	10/3/13	Pending	Hemal N. Shah, Donald R. Disney, Henrich Aurikhtentl Nannagordl
23444- 875610	0055000US	EP5- 0055	HIGH POWER GALLIUM NITRIDE ELECTRONICS USING MISCELLY SUBSTRATES	United States of America	14071032	11/4/13	Pending	Isik C. Kizilyalli, David P. Boer, Thomas R. Frundy, Guangfeng Ye
23444- 875611	0056000US	EP5- 0056	AC-DC CONVERTER WITH ADJUSTABLE OUTPUT	United States of America	14095759	12/3/13	Pending	Hemal N. Shah, Vinod Khosla
23444- 880156	0057000US	EP5- 0057	METHOD AND SYSTEM FOR INTERLEAVED BOOST CONVERTER WITH CO-PACKAGED GALLIUMNITRIDE POWER DEVICES	United States of America	14083217	11/18/13	Pending	Hemal N. Shah, Donald R. Disney

EXHIBIT C

Trademarks

Pending Applications

Mark	Country	Serial No.	Filing Date
TRUE GAN	Australia (Madrid Protocol)	1533372	11/19/12
TRUE GAN	Singapore (Madrid Protocol)	T1219939A	11/19/12
TRUE GAN	Switzerland (Madrid Protocol)	1141080	11/19/12
TRUE GAN	United States	85/661149	06/25/12
TRUE GAN	Vietnam (Madrid Protocol)	1141080	11/19/12

Issued Registrations

Mark	Country	Reg. No.	Reg. Date
TRUE GAN	China (Madrid Protocol)	1141080	11/19/12
TRUE GAN	European Community (Madrid Protocol)	1141080	11/19/12
TRUE GAN	Madrid Protocol	1141080	11/19/12
TRUE GAN	Japan (Madrid Protocol)	1141080	11/19/12
TRUE GAN	Korea (Madrid Protocol)	1141080	11/19/12

EXHIBIT D

Mask Works

N/A